



SANYO Semiconductors

DATA SHEET

An ON Semiconductor Company

MCH6605 — P-Channel Silicon MOSFET

General-Purpose Switching Device Applications

Features

- Low ON-resistance
- Ultrahigh-speed switching
- 4V drive
- Composite type with 2 MOSFETs contained in a single package, facilitating high-density mounting

Specifications

Absolute Maximum Ratings at Ta=25°C

Parameter	Symbol	Conditions	Ratings	Unit
Drain-to-Source Voltage	V _{DSS}		-50	V
Gate-to-Source Voltage	V _{GSS}		±20	V
Drain Current (DC)	I _D		-0.14	A
Drain Current (Pulse)	I _{DP}	PW≤10μs, duty cycle≤1%	-0.56	A
Allowable Power Dissipation	P _D	When mounted on ceramic substrate (900mm ² ×0.8mm)1unit	0.8	W
Channel Temperature	T _{ch}		150	°C
Storage Temperature	T _{stg}		-55 to +150	°C

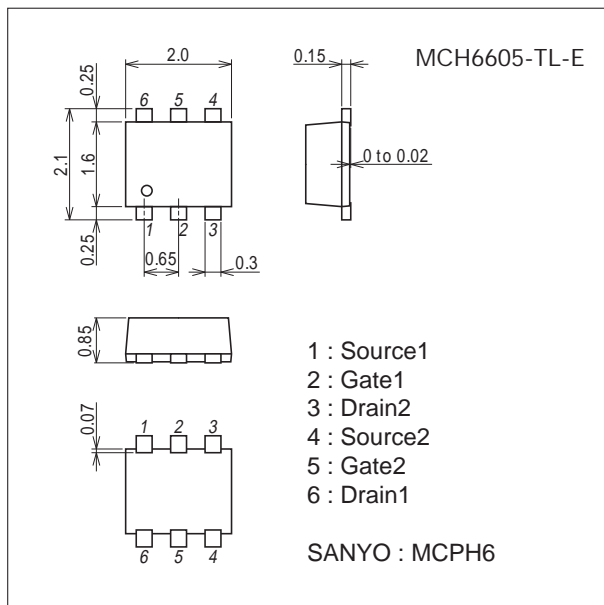
This product is designed to "ESD immunity < 200V**", so please take care when handling.

* Machine Model

Package Dimensions

unit : mm (typ)

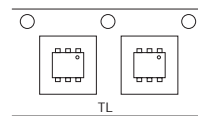
7022A-006



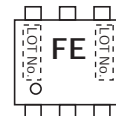
Product & Package Information

- Package : MCPH6
- JEITA, JEDEC : SC-88, SC-70-6, SOT-363
- Minimum Packing Quantity : 3,000 pcs./reel

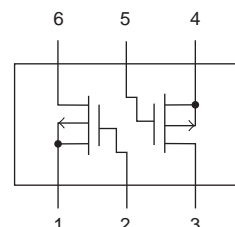
Packing Type : TL



Marking



Electrical Connection



SANYO Semiconductor Co., Ltd.

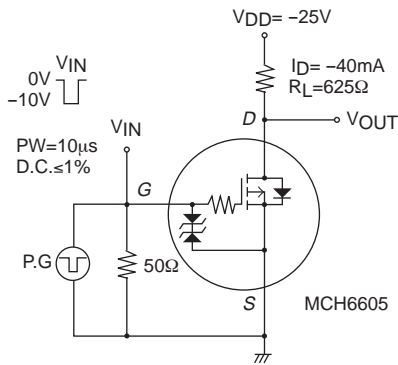
<http://semicon.sanyo.com/en/network>

MCH6605

Electrical Characteristics at Ta=25°C

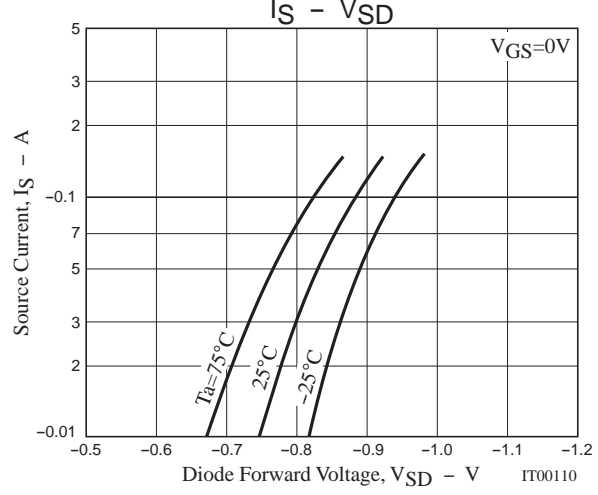
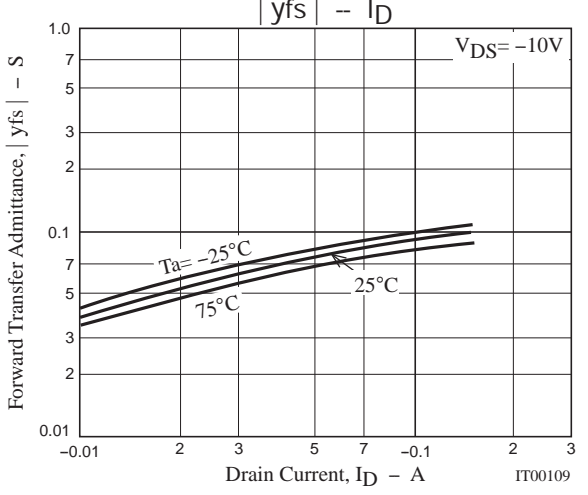
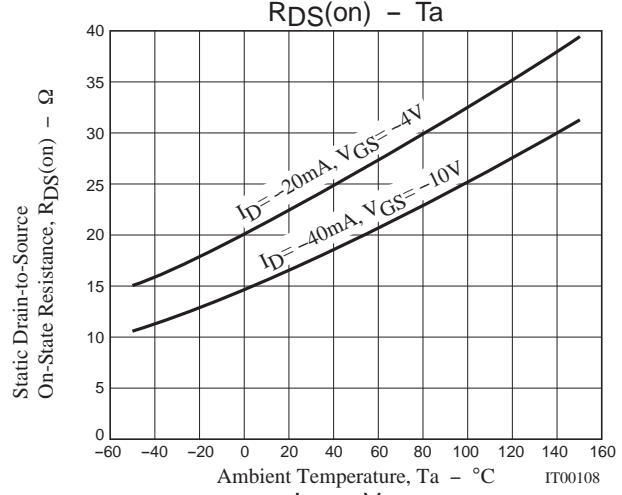
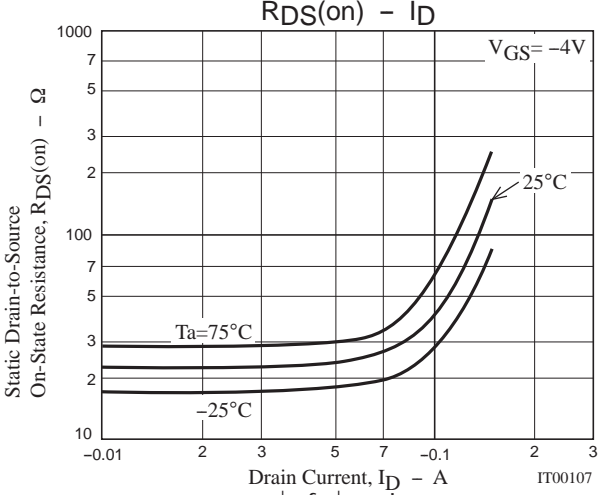
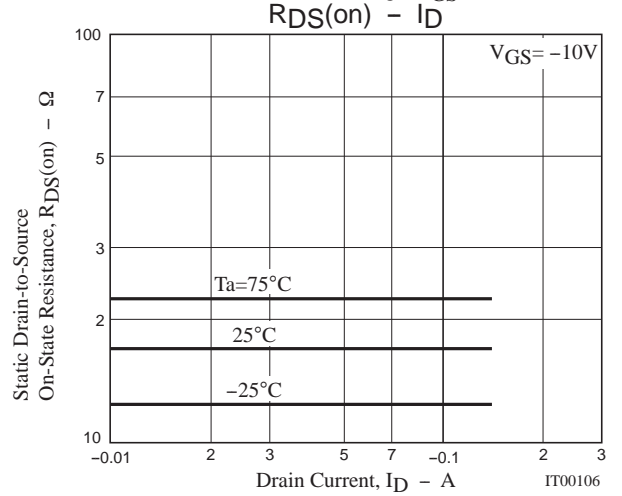
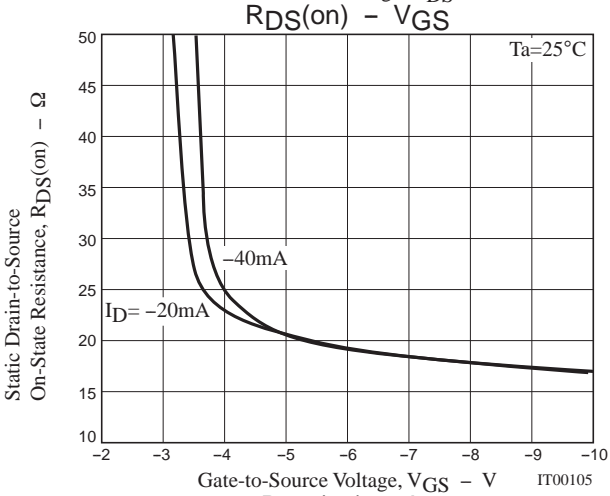
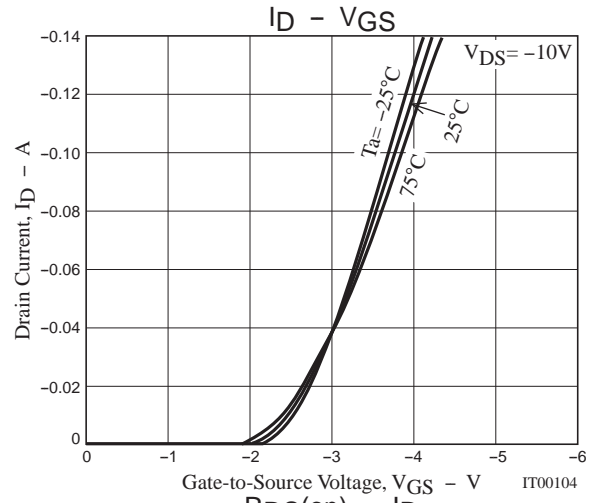
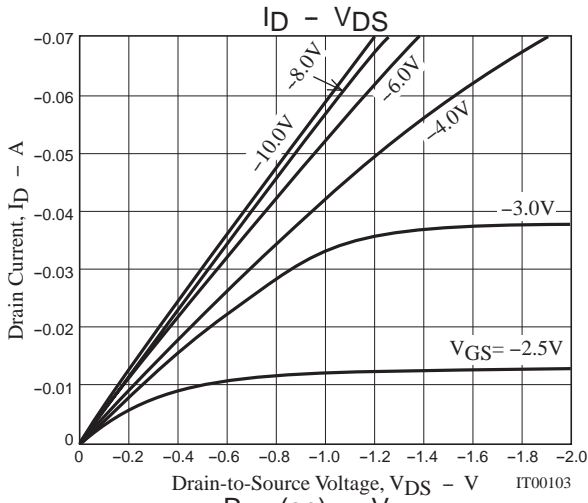
Parameter	Symbol	Conditions	Ratings			Unit
			min	typ	max	
Drain-to-Source Breakdown Voltage	V(BR)DSS	ID=1mA, VGS=0V	-50			V
Zero-Gate Voltage Drain Current	IDSS	VDS=-50V, VGS=0V			-1	μA
Gate-to-Source Leakage Current	IGSS	VGS=±16V, VDS=0V			±10	μA
Cutoff Voltage	VGS(off)	VDS=-10V, ID=-100μA	-1		-2.5	V
Forward Transfer Admittance	yfs	VDS=-10V, ID=-40mA	50	70		mS
Static Drain-to-Source On-State Resistance	RDS(on)1	ID=-40mA, VGS=-10V		17	22	Ω
	RDS(on)2	ID=-20mA, VGS=-4V		23	32	Ω
Input Capacitance	Ciss	VDS=-10V, f=1MHz		6.2		pF
Output Capacitance	Coss			4.0		pF
Reverse Transfer Capacitance	Crss			1.3		pF
Turn-ON Delay Time	td(on)			13		ns
Rise Time	tr	See specified Test Circuit.		10		ns
Turn-OFF Delay Time	td(off)			100		ns
Fall Time	tf			150		ns
Total Gate Charge	Qg			1.32		nC
Gate-to-Source Charge	Qgs	VDS=-10V, VGS=-10V, ID=-70mA		0.17		nC
Gate-to-Drain "Miller" Charge	Qgd			0.34		nC
Diode Forward Voltage	VSD		IS=-70mA, VGS=0V	-0.85	-1.2	

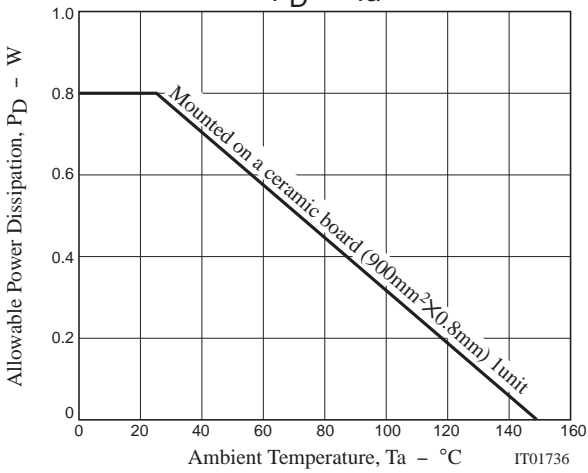
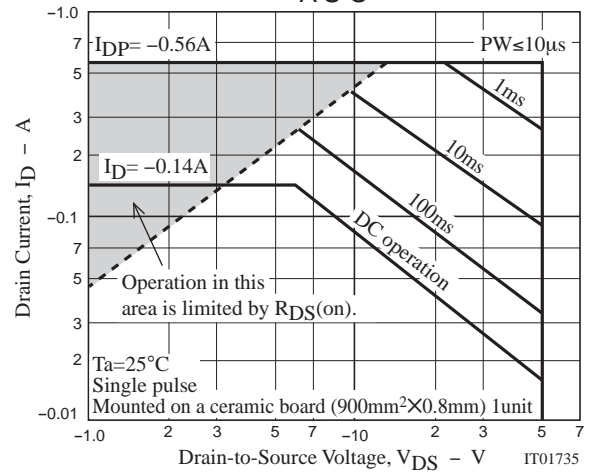
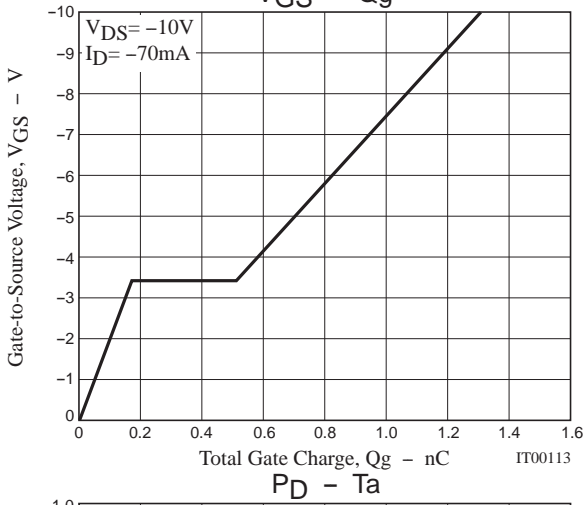
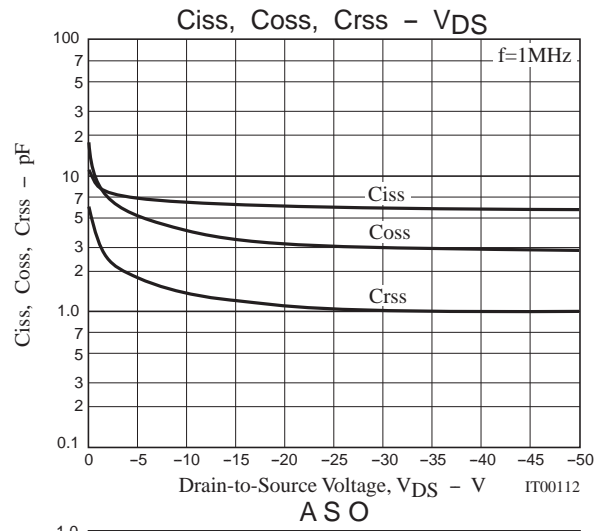
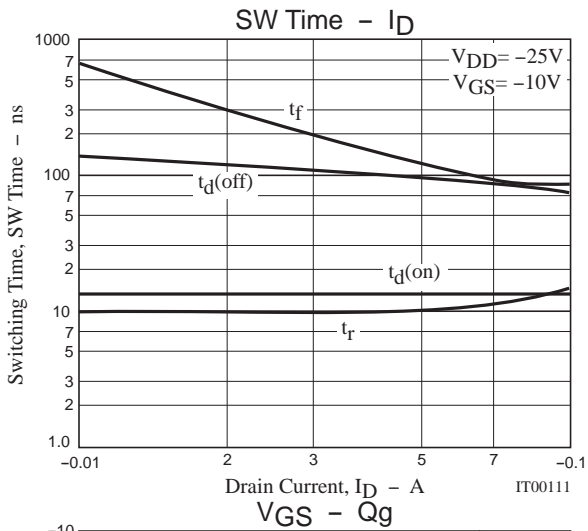
Switching Time Test Circuit



Ordering Information

Device	Package	Shipping	memo
MCH6605-TL-E	MCPH6	3,000pcs./reel	Pb Free





Taping Specification

MCH6605-TL-E

1. Packing Format

Package Name	Carrier Tape Type	Maximum Number of devices contained (pcs)			Packing format	
		Reel	Inner box	Outer box	Inner BOX (C-1)	Outer BOX (A-7)
MCPH6	MCP4	3,000	15,000	90,000	5 reels contained Dimensions:mm (external) 183×72×185	6 inner boxes contained Dimensions:mm (external) 440×195×210

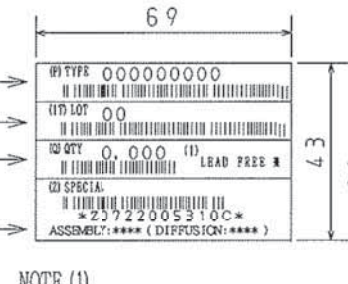
Packing method



Type No.
LOT No.
Quantity
Origin

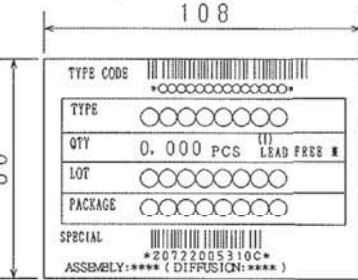
Reel label

Reel label, Inner box label
(unit:mm)



Outer box label

(It is a label at the time of factory shipments. The form of a label may change in physical distribution process.)



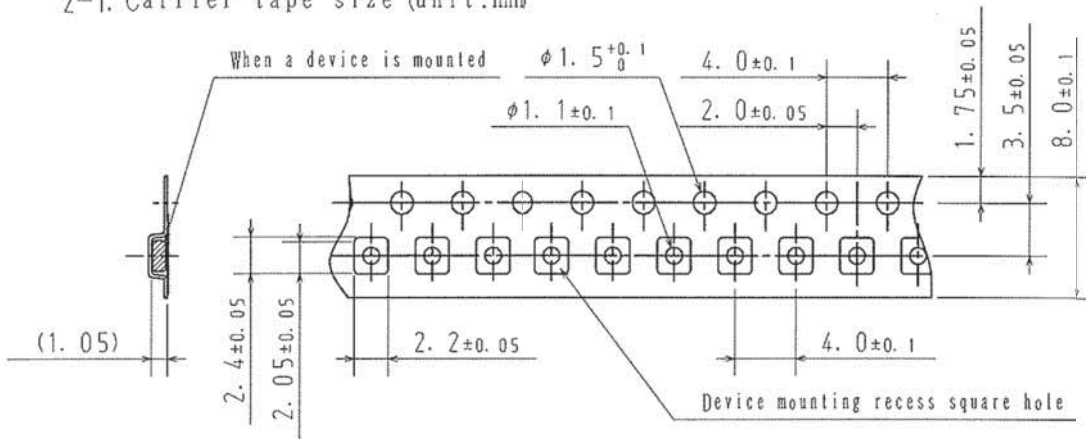
NOTE (1)

The LEAD FREE * description shows that the surface treatment of the terminal is lead free.

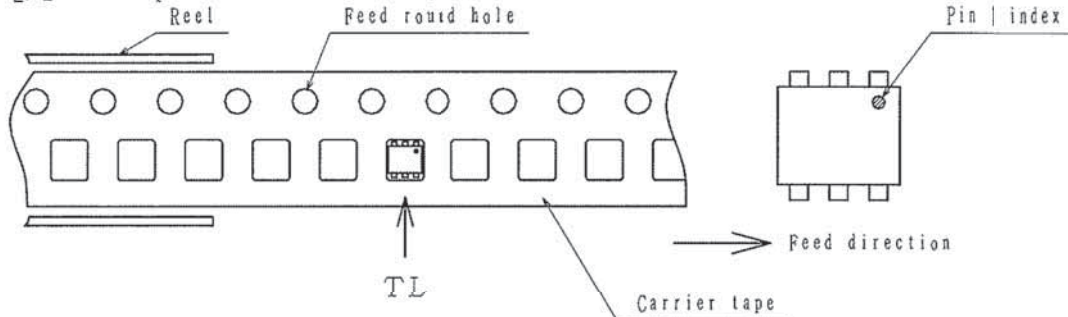
Label	JEITA Phase
LEAD FREE 3	JEITA Phase 3A
LEAD FREE 4	JEITA Phase 3

2. Taping configuration

2-1. Carrier tape size (unit:mm)



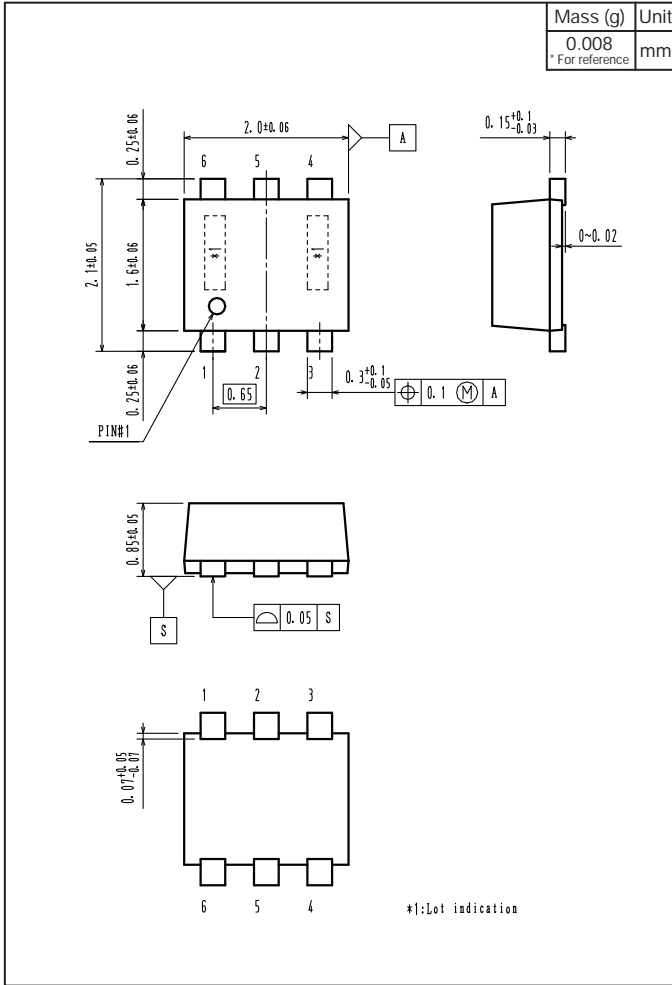
2-2. Device placement direction



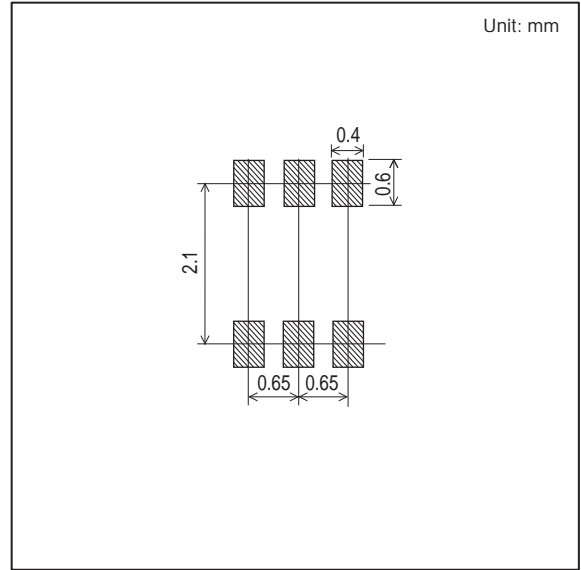
Those with pin | index on the feed hole side.....TL

MCH6605

Outline Drawing MCH6605-TL-E



Land Pattern Example



Note on usage : Since the MCH6605 is a MOSFET product, please avoid using this device in the vicinity of highly charged objects.

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